

P-Channel Enhancement-Mode MOSFET (-30V, -4.2A)

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{D(on)} (m-ohm) Max
-30V	-4.2A	53 @ V _{GS} = -10 V, I _D =-4.2A
		64 @ V _{GS} = -4.5V, I _D =-4.0A
		86 @ V _{GS} = -2.5V, I _D =-1.0A

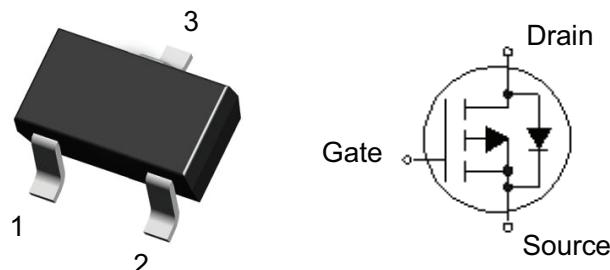
Features

- Super high dense cell trench design for low RDS(on).
- Rugged and reliable.
- SOT-23-3L package
- Ordering information : KF3021 (Lead (Pb) -free)
KF3021-G (Lead (Pb) -free and halogen-free)

KF3021 Pin Assignment & Symbol

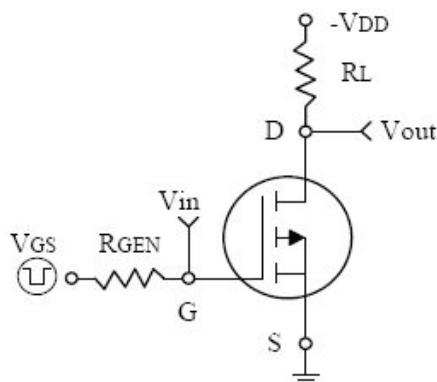
3-Lead Plastic **SOT-23-3L**

Pin 1: Gate 2: Source 3: Drain

**Absolute Maximum Ratings** ($T_A=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	± 12	V
I _D	Drain Current (Continuous)	-4.2	A
I _{DM}	Drain Current (Pulsed)	-30	A
I _S	Drain-Source Diode Forward Current ^a	-2.2	A
P _D	Total Power Dissipation @ $T_A=25^\circ\text{C}$	1.4	W
T _j , T _{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
R _{θJA}	Thermal Resistance Junction to Ambient	140	°C/W

a: Surface Mounted on FR4 Board , t ≤ 5sec .



Switching Test Circuit and Switching Waveforms